# Analog details behind the digital abstraction

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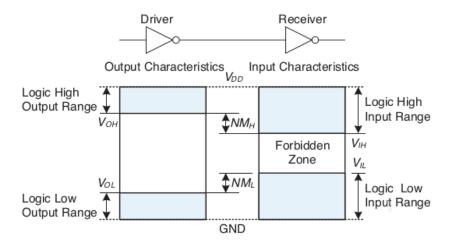
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Some of the material is out of the textbook. Additional resources include Appendix B of Brown and Vranesic book, "Fundamentals of digital logic."

### 1 Objectives

- 1. Describe how tri-state and open-collector outputs are different from totem-pole outputs
- 2. Compute noise margin of one device driving the same time
- 3. Understand timing diagrams, gate delays and critical path
- 4. Design Hazard-free two level circuits

### 2 Logic levels and Noise Margins



**Definition 1** (Supply Voltage  $(V_{DD}/V_{CC}/V_{SS})$ ).

**Definition 2** (Ground Voltage  $(V_{GND})$ ).

**Definition 3** (Input high  $(V_{IH})$  and Input Low  $(V_{IL})$  of a gate).

**Definition 4** (Output high  $(V_{OH})$  and Output low  $(V_{OL})$  of gate).

**Definition 5** (Positive logic and Negative logic).

**Definition 6** (Noise margins  $(NM_L \text{ and } NM_H)$  of a channel).

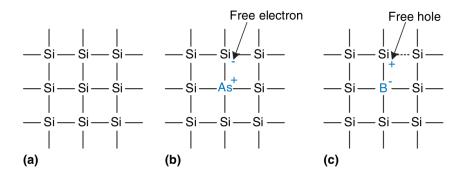


#### Example 1.

If  $V_{DD}=5V$ ,  $V_{IL}=1.35V$ ,  $V_{IH}=3.15V$ ,  $V_{OL}=0.33V$  and  $V_{OH}=3.84V$  for both the "inverters", then what are the low and high noise margins? Can the circuit tolerate 1V of noise at the channel?

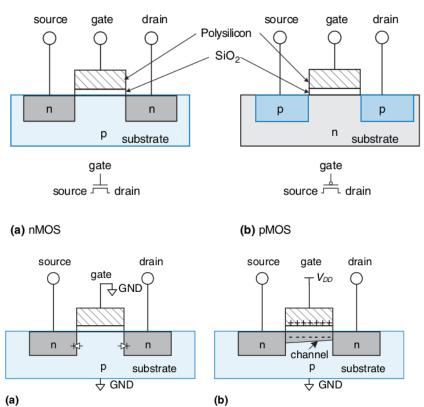
### 3 Semiconductors and Doping

Not in syllabus but good to know Elements recognized as metalloids  $V \cdot T \cdot E$ 16 13 14 15 17 В Boron Carbon Nitrogen Oxygen Fluorine Si S Cl Αl Silicon Aluminium Phosphorus Sulfur Chlorine Ga Ge As Se Br Gallium Germanium Arsenic Selenium Bromine Sb Te In Sn Indium Tin Tellurium Iodine Antimony Τl Pb Bi Po Αt Thallium Lead Bismuth Polonium Astatine Commonly recognized (86-99%): B, Si, Ge, As, Sb, Te Irregularly recognized (40-49%): Po, At Less commonly recognized (24%): Se Rarely recognized (8-10%): C, Al (All other elements cited in less than 6% of sources) Arbitrary metal-nonmetal dividing line: between Be and B, Al and Si, Ge and As, Sb and Te, Po and At

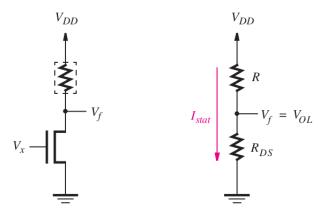


#### 4 MOSFET: Metal Oxide Field Effect Transistors

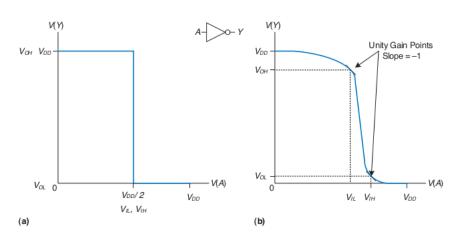
Not in syllabus but good to know

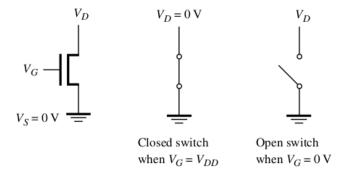


# 5 DC Transfer characteristic

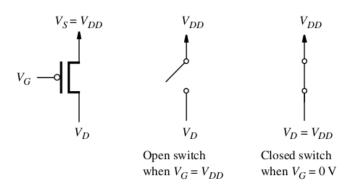


- (a) NMOS NOT gate
- (b)  $V_x = 5 \text{ V}$





#### (a) NMOS transistor

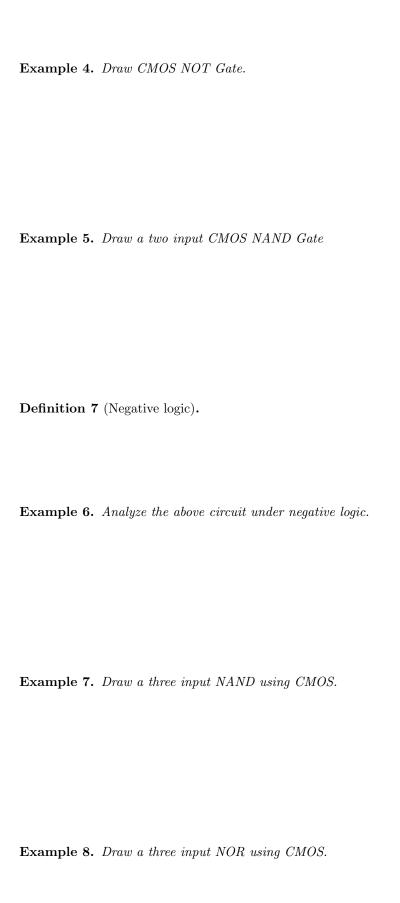


(b) PMOS transistor

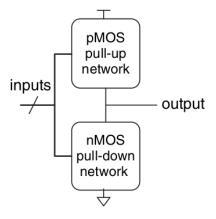
**Example 2.** Draw a NOT gate using nMOS transistors.

**Example 3.** Draw a NOT gate using pMOS transistors.

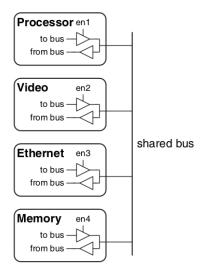
**Remark 1.** nMOS transistors pass 0's well (output between 0 and  $V_{DD} - V_t$ ). pMOS transistors pass 1's well (output between  $V_t$  and  $V_{DD}$ ).



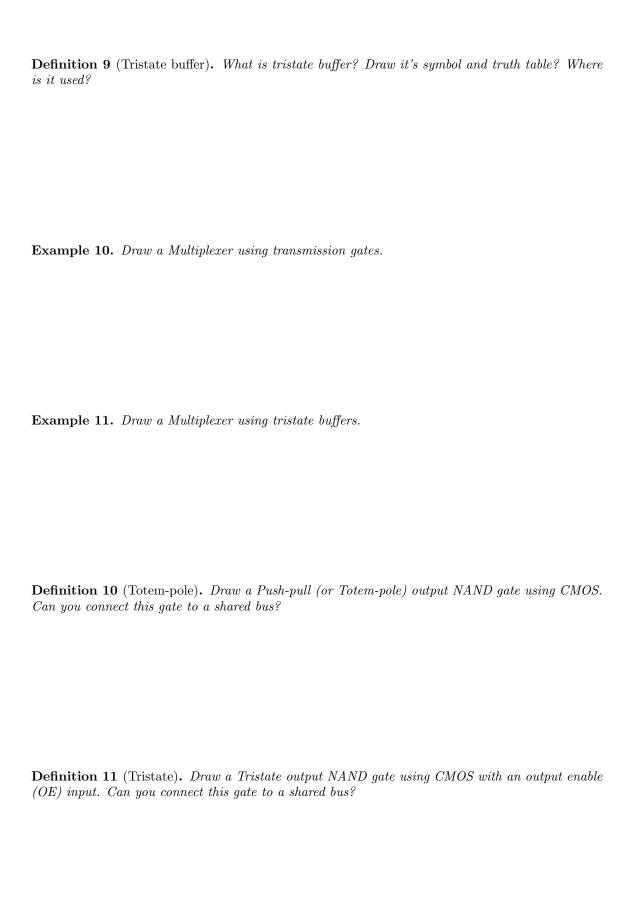
Example 9. Draw a two input AND gate using CMOS.



#### 5.1 Gates with floating output



**Definition 8** (Transmission gate). Draw a schematic of transmission gate and truth table for transmission gate. What is its commonly used symbol?



**Definition 12** (Open-collector). Draw a open-collector output NAND gate. Can you connect this gate to a shared bus?

# 6 Verilog truth tables

Table 11-11—Bitwise binary AND operator Table 11-12—Bitwise binary OR operator

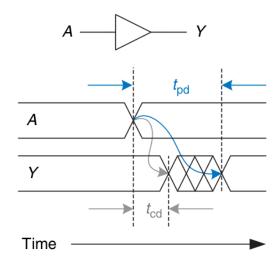
&	0	1	x	z
0	0	0	0	0
1	0	1	х	х
х	0	х	х	х
z	0	х	x	х



### 7 Timing diagrams and propagation delays

Example 12 (Timing diagram). Draw a timing diagram for an ideal NAND gate.

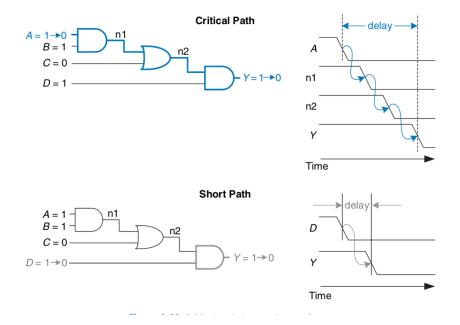
# 7.1 Delays



**Definition 13** (Propagation delay  $(t_{pd})$ ).

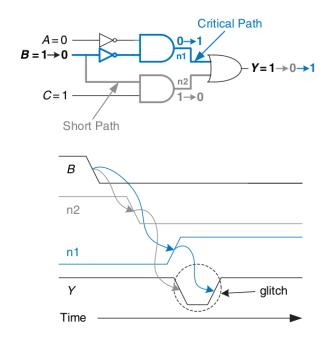
**Definition 14** (Contamination delay  $(t_{cd})$ ).

### 7.2 Paths



**Example 13.** Find the propagation delay of the circuit above given that propagation delay of each gate is 100ps add contamination delay of 60ps.

# 8 Glitches or Hazards



**Definition 15** (Glitch or Hazard).

**Example 14.** Design a circuit that fixes the glitch in the above circuit (also known as glitch-free or hazard-free circuit).